SiC MOSFET and Schottky Barrier Diode

Products:

650V, 1200V, 1700V SiC MOSFETs and SBDs, qualified according to automotive standard for discrete power devices AEC-Q101.

Applications:

High efficiency Power Supply, PV Inverter, Automotive OBC, DC/DC Converter and Traction Inverter.

Advantages:

Low Capacitance, Easy to Drive, Excellent EMI, Immunity to Noise and High Ruggedness enabled by in-house patent granted design and know how.

- $_{\circ}$ 650V/1200V/1700V SiC MOSFET, Rds(on) $\,$ 10m $\!\Omega$ to 7Ω
 - 。SMD-packages: QFN5x6, DFN8x8, DPAK (TO-252-3L), TO-263-7L, TOLL
 - 。TO-packages: TO-220, TO-220Fullpak, TO-247-3L, TO-247-4L
- 。650V/1200V SiC Schottky Barrier Diode (SBD, JBS, MPS), 4A~20A
 - 。SMD-packages: SOD-123, SMAF, QFN5x6, TO-252-2L
 - 。TO-packages: TP-220-2L, TO-220Fullpak-2L, TO-247-2L, TO-247-3L
- 。SiC MOSFET and SBD bare-die: Sawn-on-tape







